



QP CODE: 24019448

Reg No :

Name :

B.Sc DEGREE (CBCS) REGULAR / IMPROVEMENT / REAPPEARANCE EXAMINATIONS, MAY 2024

Second Semester

B.Sc Physics Model II Applied Electronics

Vocational Course - AE2VOT03 - BASICS OF POWER ELECTRONICS

2017 ADMISSION ONWARDS

6130E8ED

Time: 3 Hours Max. Marks: 80

Part A

Answer any ten questions.

Each question carries 2 marks.

- 1. Explain the formation of depletion region in a JFET.
- 2. How do you obtain I_{DSS} and V_P from the transfer characteristics curve?
- 3. Explain DC drain resistance of a JFET.
- 4. Draw the basic structure of an N channel Depletion type MOSFET.
- 5. Explain the basic principle in the working of a MOSFET.
- 6. Why is a depletion type MOSFET know as an ON MOSFET?
- 7. Write the equation for drain current in the case of an enhancement type MOSFET. Explain the terms.
- Draw and explain the circuit symbol of a P channel enhancement type MOSFET.
- 9. What do you mean by biasing? Explain the need for biasing a JFET?
- 10. Draw the circuit of voltage divider biased JFET.
- 11. What is the effect of external source resistance on the voltage gain of a common source amplifier?
- 12. List any two properties of common gate amplifier.

 $(10 \times 2 = 20)$



Page 1/3 Turn Over

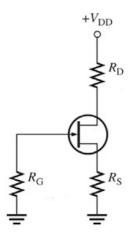


Part B

Answer any six questions.

Each question carries 5 marks.

- 13. With a neat sketch explain the structure of an N channel and a P channel JFET.
- 14. A JFET has a drain current of 15 mA. If I_{DSS} = 25 mA and V_P = 5 V, find V_{GS} .
- 15. Explain the effects of gate to source voltage on drain characteristics.
- 16. Write a short note on transfer characteristics of depletion type MOSFET.
- 17. What are the advantages of N channel MOSFET over P channel MOSFET?
- 18. What is a CMOS? What are its advantages and applications?
- 19. Find the values of drain to source voltage (V_{DS}) and gate to source voltage (V_{GS}) for the circuit shown in figure below, given I_D = 5 mA, V_{DD} = 10 V, R_D = 1 k Ω , R_S = 500 Ω .



- 20. With neat diagram explain biasing in depletion type MOSFET.
- 21. With an external drain resistance of 2 k Ω a JFET has g_m = 3 ms. Determine the value of ideal voltage gain of the common source amplifier.

 $(6 \times 5 = 30)$

Part C

Answer any two questions.

Each question carries 15 marks.

- 22. Explain the five important specification ratings with typical values of JFET and explain their practical significance.
- 23. Describe FET. Compare Junction Field Effect Transistor and a Bipolar Junction Transistor.





- 24. With neat schematic diagrams explain the working of an Enhancement type MOSFET, Draw and explain the drain characteristics.
- 25. Discuss how to set a Q point in a self-biased JFET? Also explain the setting of a Q point using D.C load line.

(2×15=30)

